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Fax Cover Sheet

DATE:

July 2, 2003

PAGES:

11 (eleven) w/cover

TO:

Examiner Tan N. Tran

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GAU 2826

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FROM:

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Message

DOCKET GS 150

Please see attached:

Response After Final Rejection

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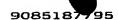
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Response after Final Rejection

Expedited Handling Requested - GAU 2826

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Patent 10/010,484

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Hshieh et al.

Serial No.:

10/010,484

Filed:

November 20, 2001

Title:

Trench MOSFET Device with Polycrystalline Silicon Source Contact Structure

Art Unit:

2826

Examiner:

Tan N. Tran

Docket No.:

GS 150

Commissioner for Patents PO Box 1450 Alexandria, VA 22313-1450

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RESPONSE AFTER FINAL REJECTION

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Sir:

In response to the final Office Action dated May 3, 2003 (Paper No. 10), kindly consider the following remarks. In addition, any deficiencies may be charged to deposit account No. 50-1047.